

Description

The DGTD120T40S1PT is produced using advanced Field Stop Trench IGBT Technology, which provides low $V_{CE(sat)}$, excellent quality and high switching performance.

Features

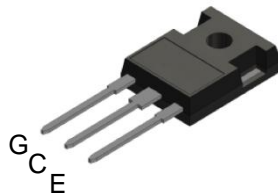
- High-Speed Switching & Low Power Loss
- $V_{CE(sat)} = 2.0V @ I_C = 40A$
- High Input Impedance
- $t_{rr} = 100ns$ (typ) @ $di_f/dt = 200A/us$
- Ultra Soft, Fast Recovery Anti-parallel Diode
- Ultra Narrowed VF Distribution Control
- **Lead-Free Finish & RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Applications

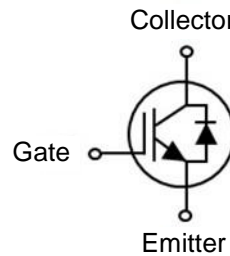
- Motor Drive
- UPS
- Solar Inverter
- IH Cooker

Mechanical Data

- Case: TO-247 (Type MC)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 ^(E3)
- Weight: 5.6 grams (Approximate)



TO-247



Device Symbol

Ordering Information (Note 4)

Product	Marking	Quantity
DGTD120T40S1PT	DGTD120T40S1	450 per Box in Tubes (Note 5)

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
 5. 30 Devices per Tube

Marking Information



- ⌋⌋ = Manufacturer's Marking
- DGTD120T40S1 = Product Type Marking Code
- YY = Year (ex: 18 = 2018)
- LLLLL = Lot Code
- WW = Week (01 to 53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CE}	1200	V
DC Collector Current	I _C	T _C = 25°C	80
		T _C = 100°C	40
Pulsed Collector Current, t _p limited by T _{vjmax}	I _{CM}	160	A
Diode Forward Current	I _F	T _C = 25°C	80
		T _C = 100°C	40
Diode Pulsed Current, t _p limited by T _{vjmax}	I _{FM}	160	A
Gate-Emitter Voltage	V _{GES}	±20	V
Short Circuit Withstand Time V _{CC} ≤ 600V, V _{GE} = 15V, T _{vj} = 150°C Allowed Number of Short Circuits < 1000 Time Between Short Circuits ≥ 1.0s	t _{sc}	10	μs

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 6)	P _D	T _C = 25°C	357
		T _C = 100°C	142
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	40	°C/W
Thermal Resistance, Junction to Case for IBGT (Note 6)	R _{θJC}	0.35	
Thermal Resistance, Junction to Case for Diode (Note 6)	R _{θJC}	0.80	
Operating Temperature	T _{vj}	-55 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	

Note: 6. When mounted on a standard JEDEC 2-layer FR-4 board.

Electrical Characteristics (@ $T_{vj} = +25^{\circ}\text{C}$, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Condition	
STATIC CHARACTERISTICS							
Collector-Emitter Breakdown Voltage	BV_{CES}	1,200	–	–	V	$I_C = 1\text{mA}, V_{GE} = 0\text{V}$	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$T_{vj} = 25^{\circ}\text{C}$	–	2.00	2.40	V	$I_C = 40\text{A}, V_{GE} = 15\text{V}$
		$T_{vj} = 150^{\circ}\text{C}$	–	2.45	–		
Diode Forward Voltage	V_F	$T_{vj} = 25^{\circ}\text{C}$	–	2.40	3.00	V	$I_F = 40\text{A}$
		$T_{vj} = 150^{\circ}\text{C}$	–	2.45	–		
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	4.5	5.5	6.5	V	$V_{CE} = V_{GE}, I_C = 1\text{mA}$	
Zero Gate Voltage Collector Current	I_{CES}	–	–	1.0	mA	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}$	
Gate-Emitter Leakage Current	I_{GES}	–	–	± 250	nA	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$	
DYNAMIC CHARACTERISTICS							
Total Gate Charge	Q_g	–	341	–	nC	$V_{CE} = 600\text{V}, I_C = 40\text{A}, V_{GE} = 15\text{V}$	
Gate-Emitter Charge	Q_{ge}	–	52	–			
Gate-Collector Charge	Q_{gc}	–	126	–			
Input Capacitance	C_{ies}	–	6,030	–	pF	$V_{CE} = 30\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	
Reverse Transfer Capacitance	C_{res}	–	107	–			
Output Capacitance	C_{oes}	–	206	–			
SWITCHING CHARACTERISTICS							
Turn-on Delay Time	$t_{d(on)}$	–	65	–	ns	$V_{GE} = 15\text{V}, V_{CC} = 600\text{V}, I_C = 40\text{A}, R_G = 10\Omega, \text{Inductive Load}, T_{vj} = 25^{\circ}\text{C}$	
Rise time	t_r	–	55	–			
Turn-off Delay Time	$t_{d(off)}$	–	308	–			
Fall Time	t_f	–	40	–			
Turn-on Switching Energy	E_{on}	–	1.96	–	mJ		
Turn-off Switching Energy	E_{off}	–	0.54	–			
Total Switching Energy	E_{ts}	–	2.50	–			
Reverse Recovery Time	t_{rr}	–	100	–	ns		$I_F = 40\text{A}, di_F/dt = 200\text{A}/\mu\text{s}, T_{vj} = 25^{\circ}\text{C}$
Reverse Recovery Current	I_{rr}	–	7	–	A		
Reverse Recovery Charge	Q_{rr}	–	350	–	nC		
Turn-on Delay Time	$t_{d(on)}$	–	70	–	ns	$V_{GE} = 15\text{V}, V_{CC} = 600\text{V}, I_C = 40\text{A}, R_G = 10\Omega, \text{Inductive Load}, T_{vj} = 150^{\circ}\text{C}$	
Rise time	t_r	–	62	–			
Turn-off Delay Time	$t_{d(off)}$	–	325	–			
Fall Time	t_f	–	62	–			
Turn-on Switching Energy	E_{on}	–	2.35	–	mJ		
Turn-off Switching Energy	E_{off}	–	1.61	–			
Total Switching Energy	E_{ts}	–	3.96	–			
Reverse Recovery Time	t_{rr}	–	180	–	ns		$I_F = 40\text{A}, di_F/dt = 200\text{A}/\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$
Reverse Recovery Current	I_{rr}	–	10	–	A		
Reverse Recovery Charge	Q_{rr}	–	900	–	nC		

Typical Performance Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

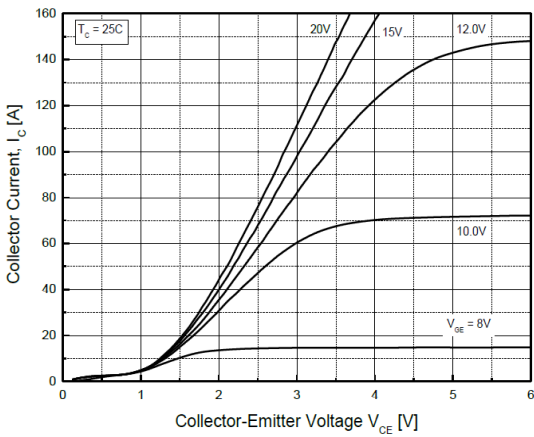


Fig.1 Typical Output Characteristics

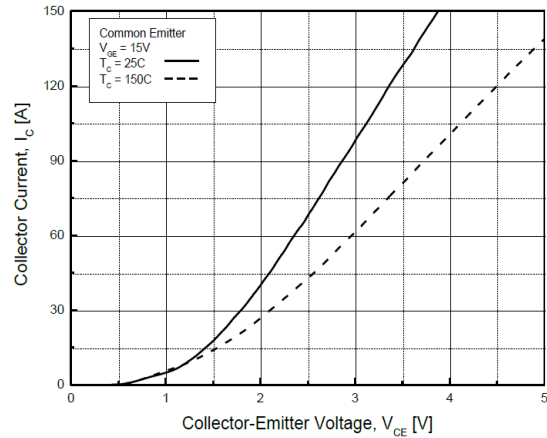


Fig.2 Typical Collector-Emitter Saturation Voltage

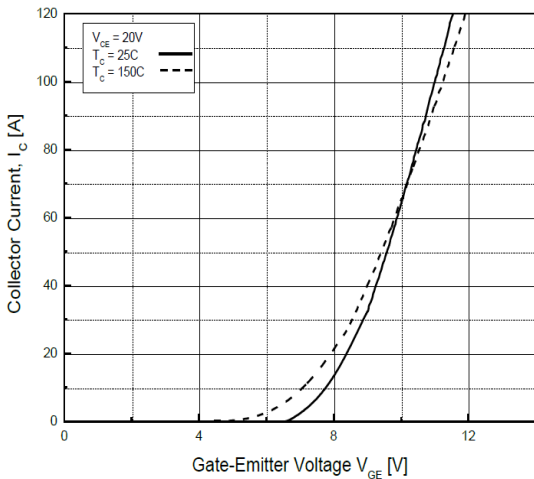


Fig.3 Typical Transfer Characteristics

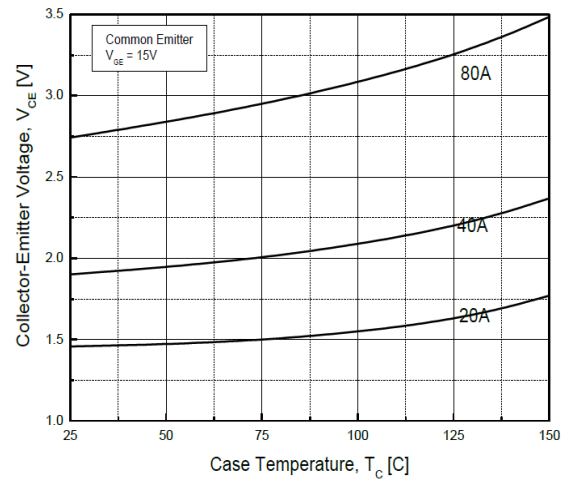


Fig.4 Typical Collector-Emitter Saturation Voltage at Case Temperature

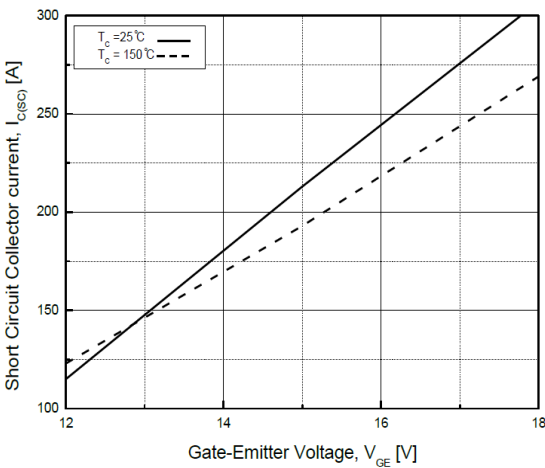


Fig.5 Typical Short Circuit Collector Current

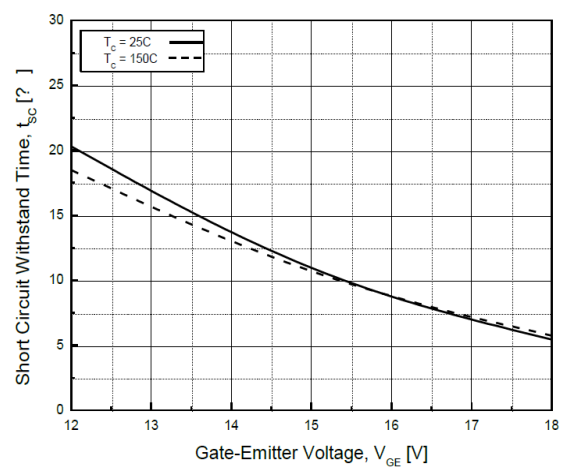


Fig.6 Typical Short Circuit Withstand Time

Typical Performance Characteristics (continued)

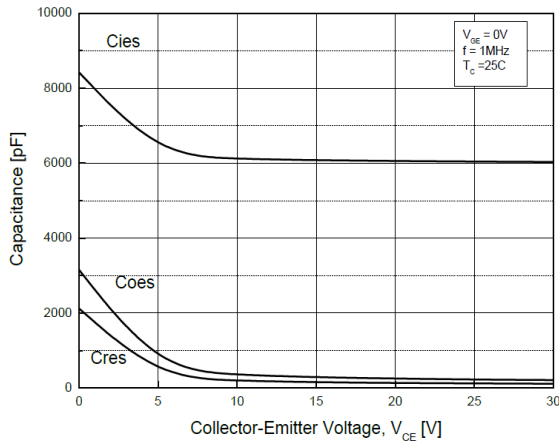


Fig.7 Typical Capacitance

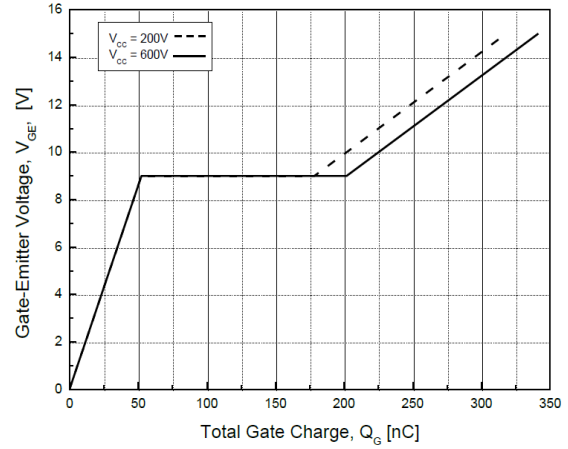


Fig.8 Typical Gate Charge

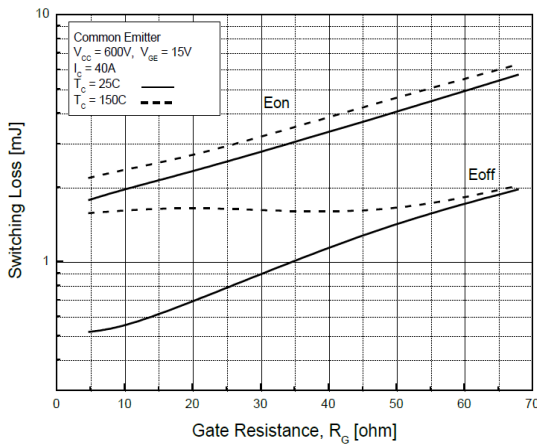


Fig.9 Switching Loss-Gate Resistance

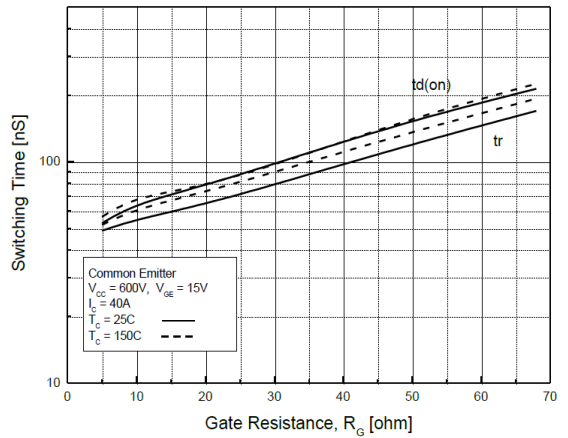


Fig.10 Turn on Characteristics-Gate Resistance

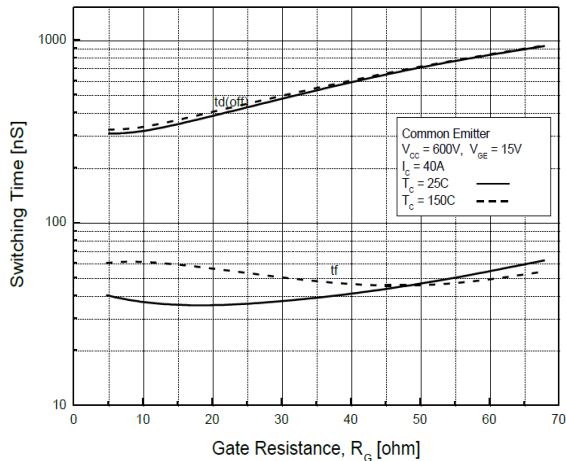


Fig.11 Turn off Characteristics-Gate Resistance

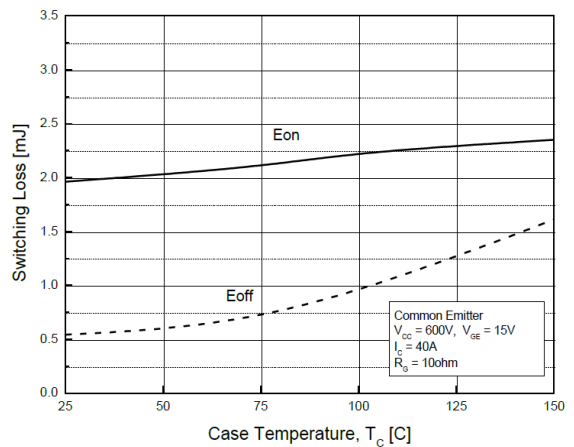


Fig.12 Switching Loss-Case Temperature

Typical Performance Characteristics (cont.)

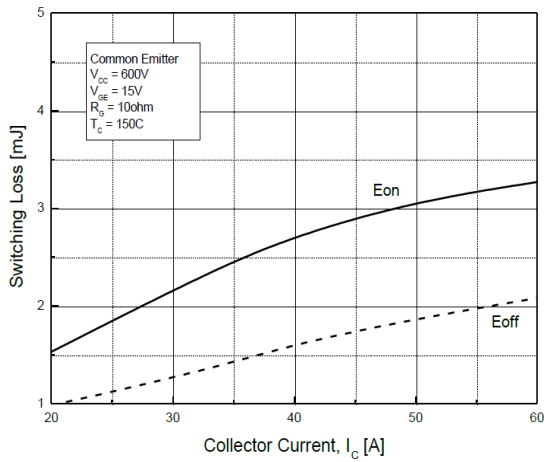


Fig.13 Switching Loss-Collector Current

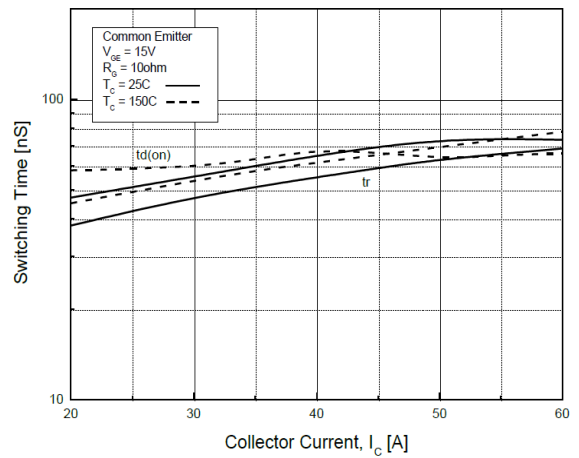


Fig.14 Typical Turn on-Collector Current

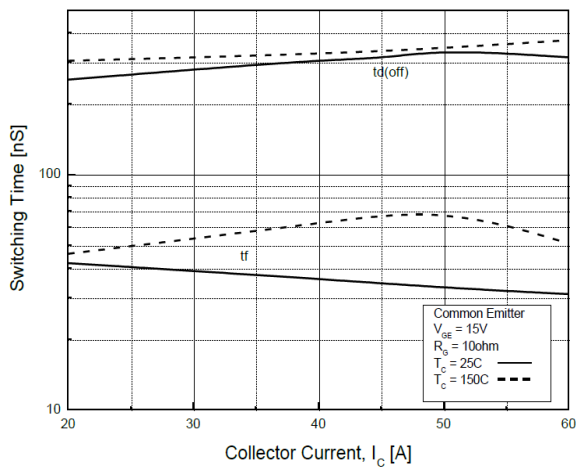


Fig.15 Typical Turn off-Collector Current

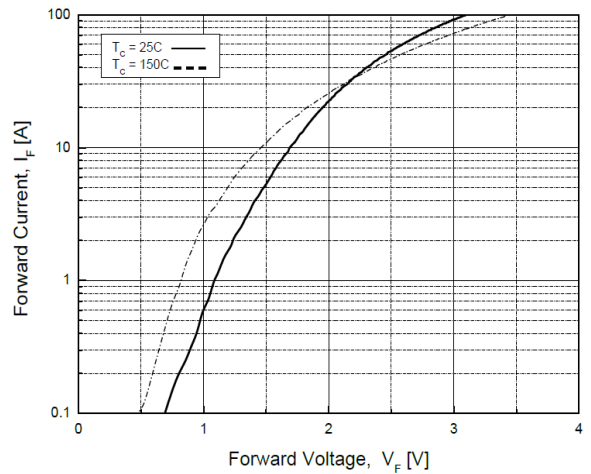


Fig.16 Diode Forward Characteristics

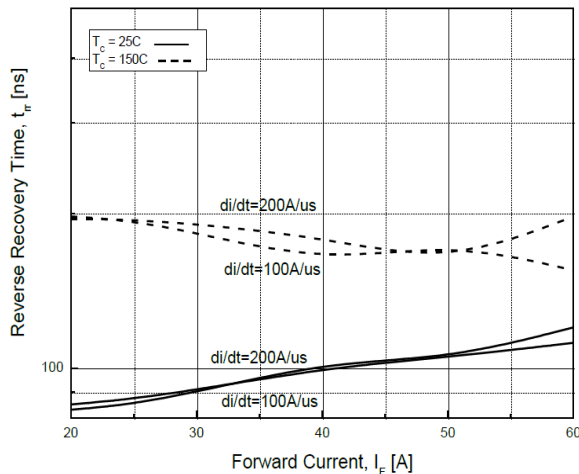


Fig.17 Typical Turn off-Collector Current

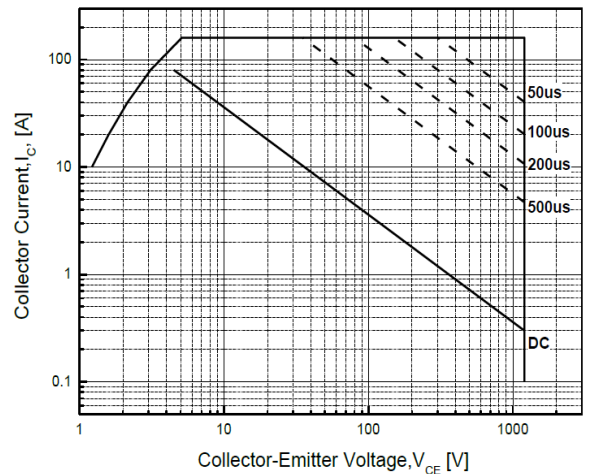


Fig.18 Forward Bias Safe Operating Area

Typical Performance Characteristics (cont.)

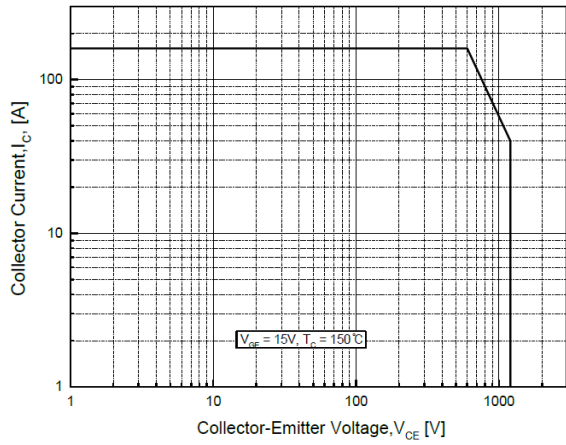


Fig.19 Reverse Bias Safe Operating Area

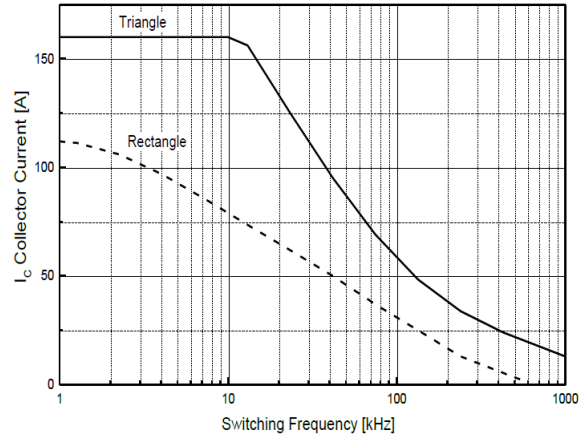


Fig.20 Switching frequency – Collector current

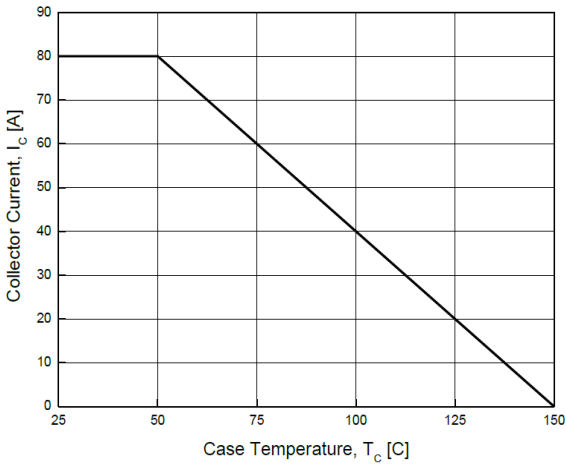


Fig.21 Case Temperature – Collector Current

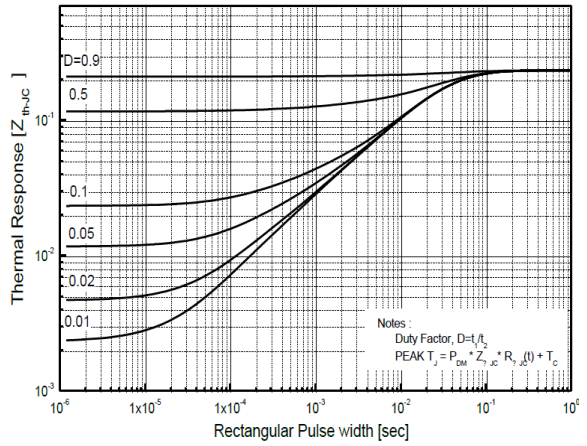
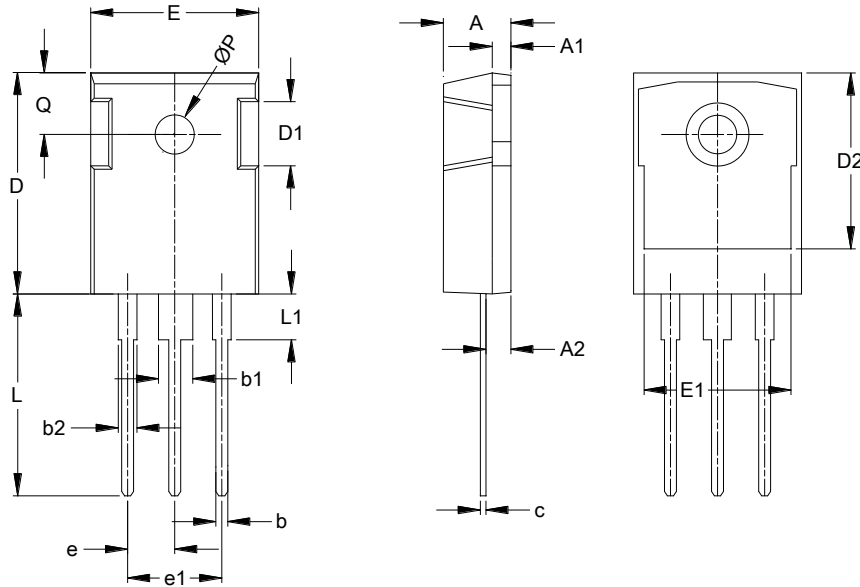


Fig.22 IGBT Transient Thermal Impedance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO-247 (Type MC)



TO-247			
Dim	Min	Max	Typ
A	4.700	5.310	-
A1	1.500	2.490	-
A2	2.200	2.600	-
b	0.990	1.400	-
b1	2.590	3.430	-
b2	1.650	2.390	-
c	0.380	0.890	-
D	20.30	21.46	-
D1	4.320	5.490	-
D2	13.08	-	-
E	15.45	16.26	-
E1	13.06	14.02	-
e	5.450		
e1	10.90		
L	19.81	20.57	-
L1	-	4.500	-
Q	5.380	6.200	-
øP	3.500	3.700	-
All Dimensions in mm			

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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